

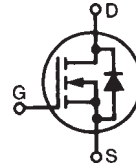
HiPerFET™ Power MOSFETs Q2-Class

IXFK 38N80Q2
IXFN 38N80Q2
IXFX 38N80Q2

V_{DSS} = 800 V
I_{D25} = 38 A
R_{DS(on)} = 220 mΩ

t_{rr} ≤ 250 ns

N-Channel Enhancement Mode
Avalanche Rated, High dv/dt, Low Q_g
Low intrinsic R_g

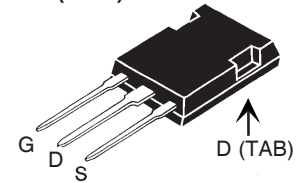


Preliminary Data Sheet

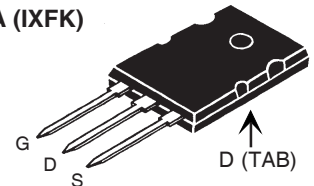
Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 150°C	800	V
V _{DGR}	T _J = 25°C to 150°C; R _{GS} = 1 MΩ	800	V
V _{GS}	Continuous	±30	V
V _{GSM}	Transient	±40	V
I _{D25}	T _C = 25°C	38	A
I _{DM}	T _C = 25°C, pulse width limited by T _{JM}	150	A
I _{AR}	T _C = 25°C	38	A
E _{AR}	T _C = 25°C	75	mJ
E _{AS}	T _C = 25°C	4.0	J
dv/dt	I _S ≤ I _{DM} , di/dt ≤ 100 A/μs, V _{DD} ≤ V _{DSS} , T _J ≤ 150°C, R _G = 2 Ω	20	V/ns
P _D	T _C = 25°C	735	W
T _J		-55 ... +150	°C
T _{JM}		150	°C
T _{stg}		-55 ... +150	°C
T _L	1.6mm (0.063in) from case for 10s (Plus247, TO-264)	300	°C
V _{ISOL}	50/60Hz, RMS t=1 min I _{ISOL} < 1mA t=1s	SOT-227B 2500 3000	V~ V~
M _d	Mounting torque Terminal torque	TO-264 SOT-227B	0.9/8 Nm/lb.in. 1.5/13 Nm/lb.in.
F _c	Mounting force	PLUS-247	22...130/5...30 N/lb
Weight		PLUS247	g
		TO-264	10 g
		SOT-227B	30 g

Symbol	Test Conditions	Characteristic Values (T _J = 25°C, unless otherwise specified)		
		min.	typ.	max.
V _{DSS}	V _{GS} = 0 V, I _D = 3mA	800		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 8 mA	2.0		V
I _{GSS}	V _{GS} = ±30 V _{DC} , V _{DS} = 0			±200 nA
I _{DSS}	V _{DS} = V _{DSS} V _{GS} = 0 V	T _J = 25°C		50 μA
		T _J = 125°C		2 mA
R _{DS(on)}	V _{GS} = 10 V, I _D = 0.5 • I _{D25} Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			220 mΩ

PLUS247™ (IXFX)

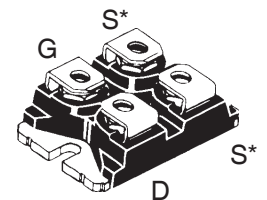


TO-264 AA (IXFK)



miniBLOC, SOT-227 B (IXFN)

E153432



* Either Source terminal can be used as main or Kelvin source terminal

G = Gate D = Drain
S = Source TAB = Drain

Features

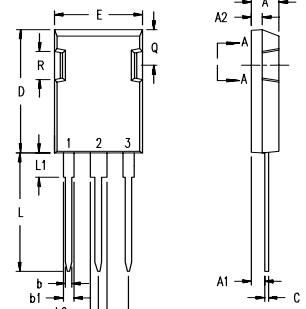
- Double metal process for low gate resistance
- International standard packages
- Epoxy meet UL 94 V-0, flammability classification
- Avalanche energy and current rated
- Fast intrinsic Rectifier
- miniBLOC package version with Aluminum Nitrate isolation

Advantages

- Easy to mount
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	25	37	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		8340	pF
C_{oss}			890	pF
C_{rss}			175	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1.0\ \Omega$ (External),		20	ns
t_r			16	ns
$t_{d(off)}$			60	ns
t_f			12	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		190	nC
Q_{gs}			44	nC
Q_{gd}			88	nC
R_{thJC}	TO-264			0.17 K/W
R_{thCK}			0.15	K/W

PLUS 247™ Outline



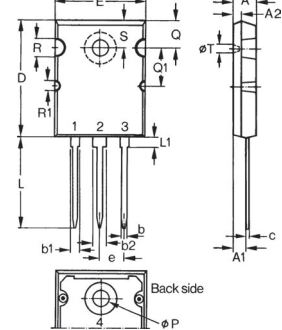
Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)
4 - Drain (Collector)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC		.215 BSC	
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

Source-Drain Diode

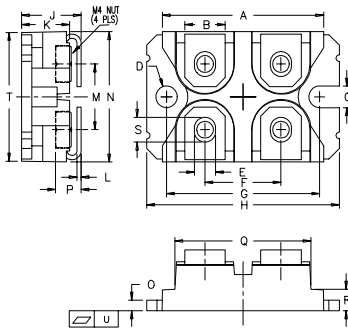
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			38 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			150 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$			250 ns
Q_{RM}			1	μC
I_{RM}			10	A

TO-264 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

SOT-227B miniBLOC Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	

Fig. 1. Output Characteristics @ 25°C

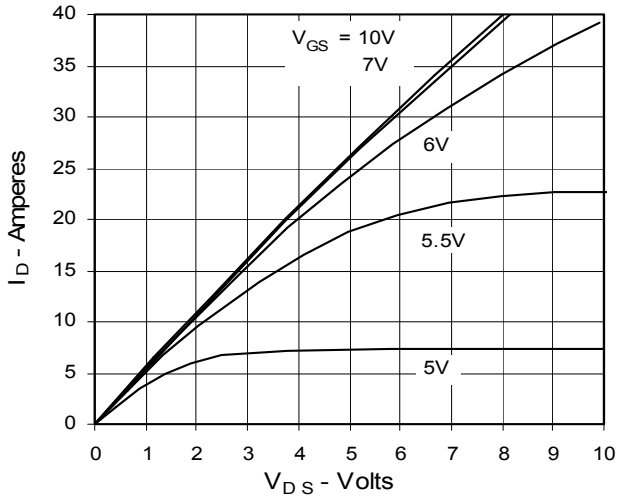


Fig. 2. Extended Output Characteristics @ 25°C

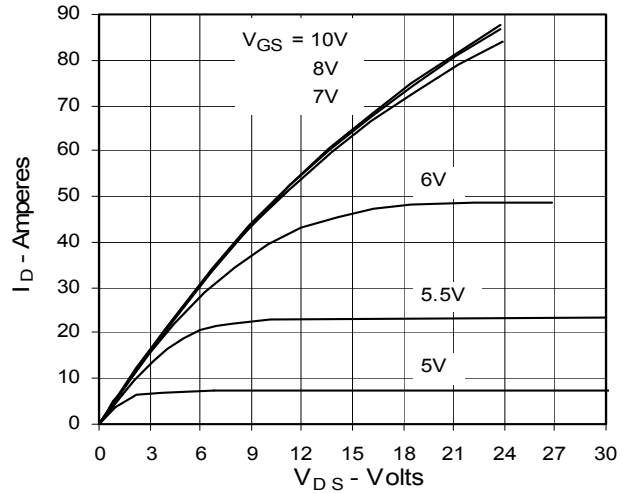


Fig. 3. Output Characteristics @ 125°C

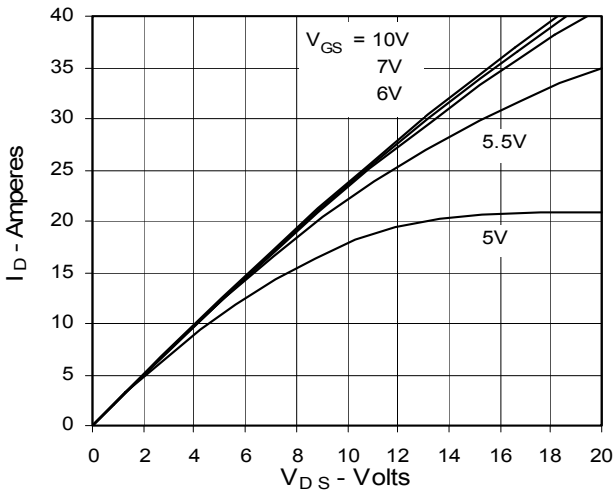


Fig. 4. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. Junction Temperature

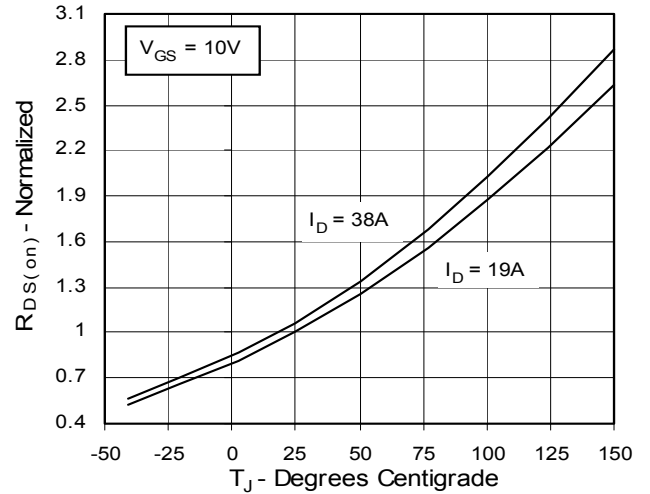


Fig. 5. $R_{DS(on)}$ Normalized to 0.5 I_{D25} Value vs. I_D

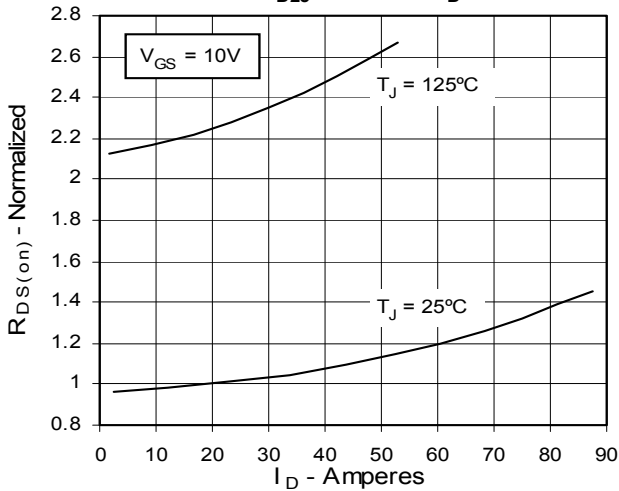


Fig. 6. Drain Current vs. Case Temperature

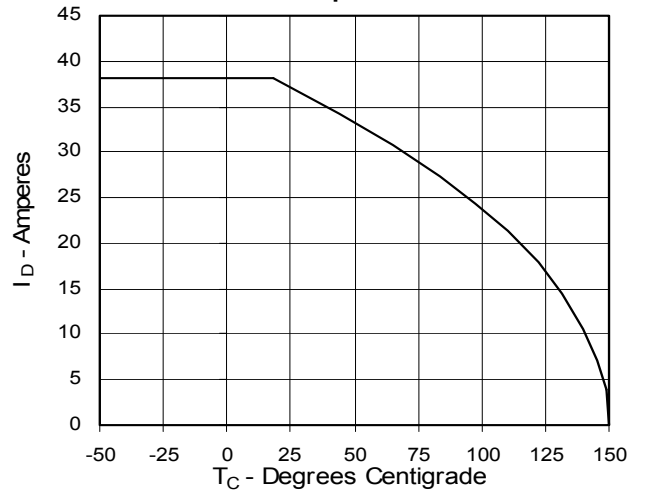


Fig. 7. Input Admittance

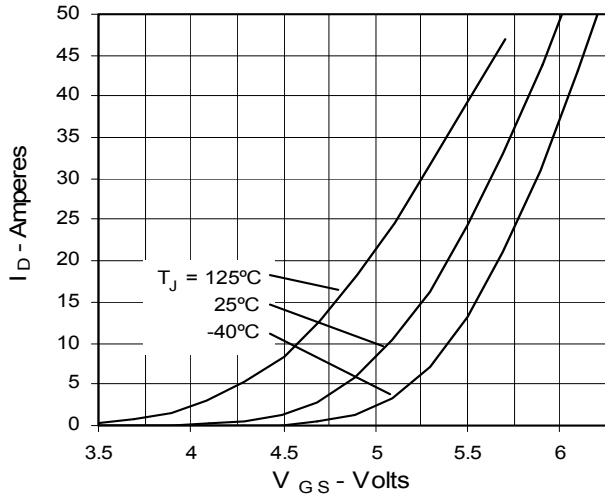


Fig. 8. Transconductance

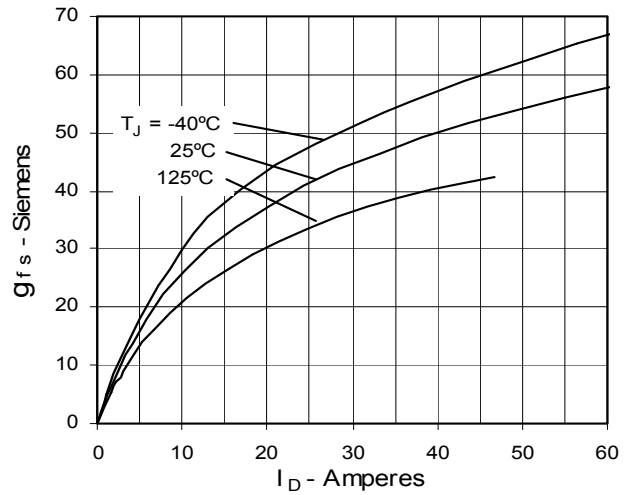


Fig. 9. Source Current vs. Source-To-Drain Voltage

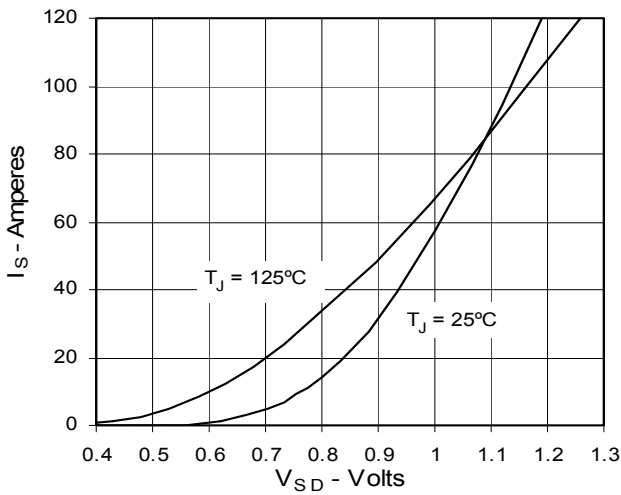


Fig. 10. Gate Charge

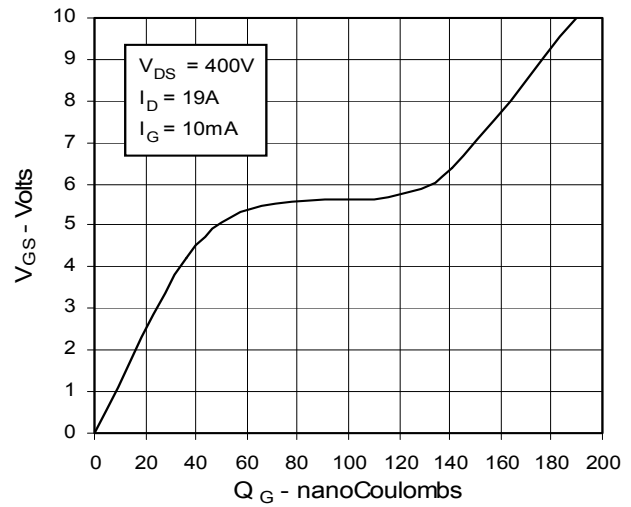


Fig. 11. Capacitance

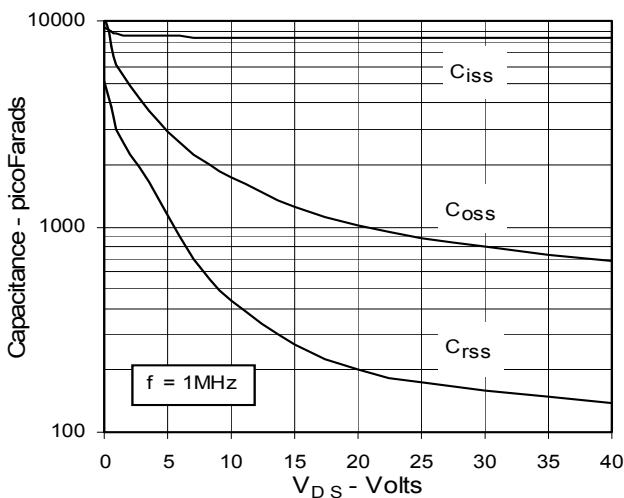


Fig. 12. Forward-Bias Safe Operating Area

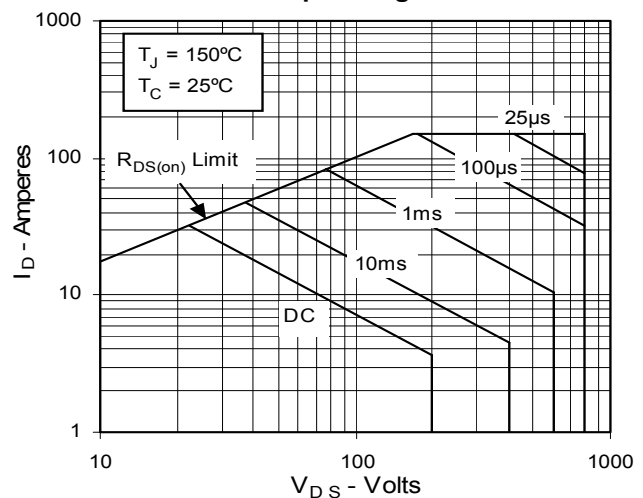


Fig. 13. Maximum Transient Thermal Resistance

